



40V +175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D T _A = +25°C
40\/	$15m\Omega$ @ $V_{GS} = 10V$	8.6A
40V	$20m\Omega$ @ $V_{GS} = 4.5V$	7.5A

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Qg Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

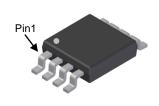
Description and Applications

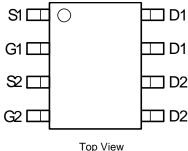
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

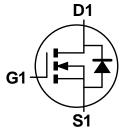
- Engine Management Systems
- Body Control
- DC-DC Converters

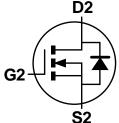
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.074 grams (Approximate)









Top View
Pin Configuration

Equivalent Circuit

Ordering Information (Note 5)

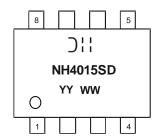
Top View

Part Number	Case	Packaging
DMNH4015SSDQ-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



⊃;; = Manufacturer's Marking
 NH4015SD = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 16 = 2016)
 WW = Week (01 - 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	40	V		
Gate-Source Voltage			V_{GSS}	±20	V
State $T_{\Delta} = +70$		$T_A = +25$ °C $T_A = +70$ °C	I _D	8.6 6.9	А
Continuous Drain Current (Note 7) V _{GS} = 10V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	11.0 8.8	А
Maximum Body Diode Forward Current (Note 7)	Is	2.2	Α		
Pulsed Drain Current (380µs pulse, duty cycle = 1%)	I _{DM}	80	Α		
Avalanche Current (Note 8) L = 0.1mH	I _{AS}	25	Α		
Avalanche Energy (Note 8) L = 0.1mH	E _{AS}	33	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 6)	T _A = +25°C	Pn	1.4	W
Total Fower Dissipation (Note o)	T _A = +70°C	PD	0.9	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	D	111	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	66	
Total Power Dissipation (Note 7)	$T_A = +25$ °C	D-	2.0	W
Total Fower Dissipation (Note 1)	$T_A = +70^{\circ}C$	P _D	1.2	
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	В	75	
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{\theta JA}$	45	°C/W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	10.4		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = ±25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	•			•			
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D	_	10	15	mΩ	$V_{GS} = 10V, I_D = 12A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	12	20	11122	$V_{GS} = 4.5V, I_D = 10A$	
Diode Forward Voltage	V_{SD}	_	0.7	1.0	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}		1,938	-		V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss		156	-	pF		
Reverse Transfer Capacitance	Crss		126	-			
Gate Resistance	R_{G}	_	1.8	3.2	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	15	-			
Total Gate Charge (V _{GS} = 10V)	Qg	_	33	-	nC	Vps = 15V, lp = 12A	
Gate-Source Charge	Q_{gs}	_	4.4	-	110	VDS = 15V, ID = 12A	
Gate-Drain Charge	Q_{gd}	_	5.9	-			
Turn-On Delay Time	t _{D(on)}	_	4.4	-			
Turn-On Rise Time	t _r	_	10.5	-	nS	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(off)}	_	12.3	-	113	$R_L=1.25\Omega,\ R_G=3\Omega,$	
Turn-Off Fall Time	t _f		5.7	-			
Body Diode Reverse Recovery Time	t _{rr}		11	_	nS	100 41/44 5000///-	
Body Diode Reverse Recovery Charge	Qrr	_	7.6	_	nC	$I_S = 12A$, $dI/dt = 500A/\mu s$	

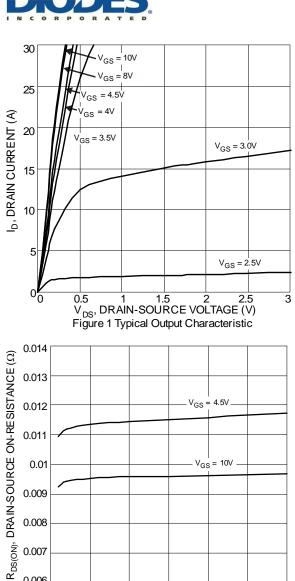
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. Notes:

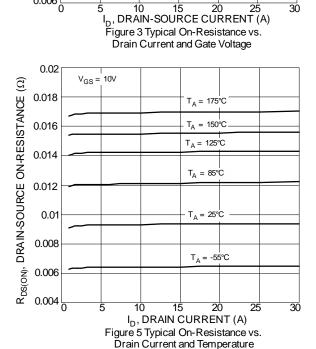
^{8.} I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep TJ = +25°C.

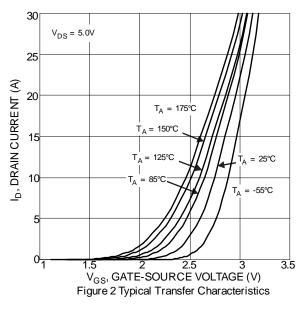
^{9.} Short duration pulse test used to minimize self-heating effect.

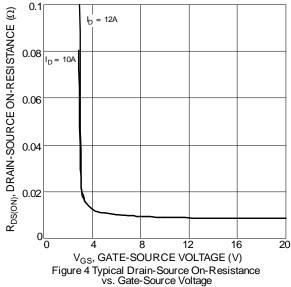
^{10.} Guaranteed by design. Not subject to product testing.

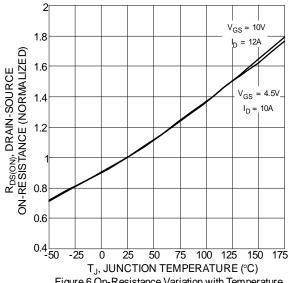










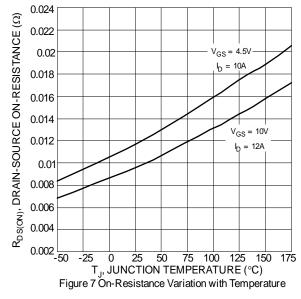


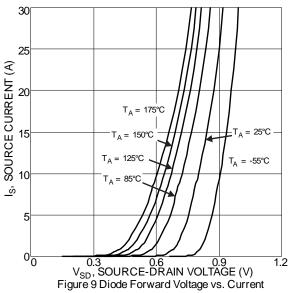
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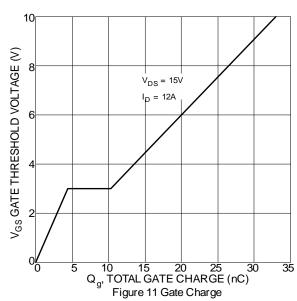
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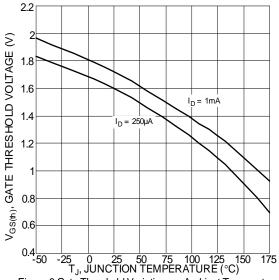
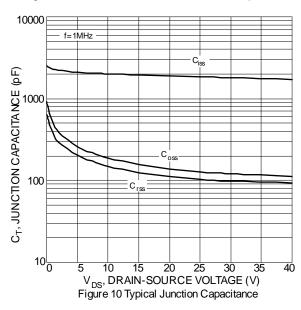
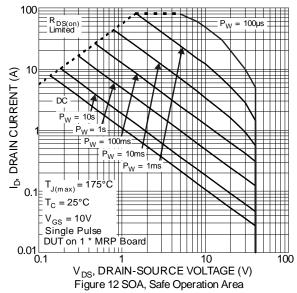
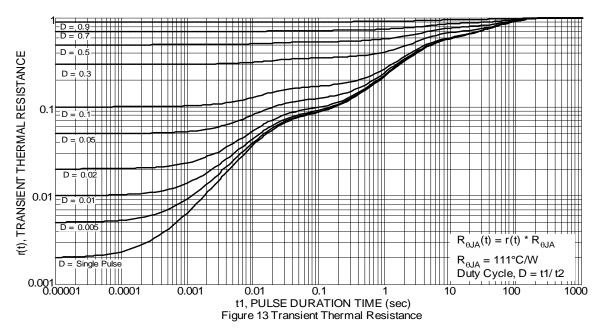


Figure 8 Gate Threshold Variation vs. Ambient Temperature





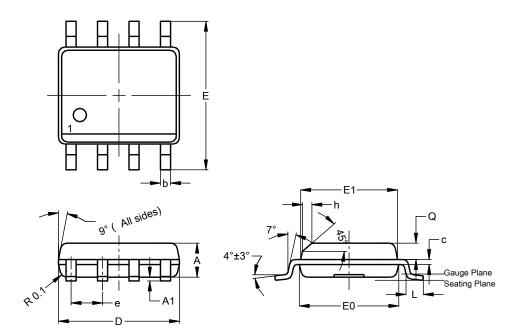




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8

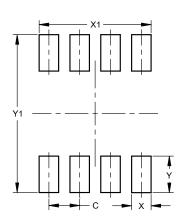


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
q	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е	1		1.27		
h			0.35		
Г	0.62	0.82	0.72		
Ø	0.60	0.70	0.65		
All Dimensions in mm					



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8

Dimensions	Value (in mm)				
С	1.27				
Х	0.802				
X1	4.612				
Y	1.505				
Y1	6.50				

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